

N-channel silicon junction field-effect transistors Rev. 4 — 15 September 2011 Proc

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage.

### 1.3 Applications

- Impedance converters in e.g. electret microphones and infrared detectors
- VHF amplifiers in oscillators and mixers.

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage (DC)		-	-	±30	V
V <sub>GSoff</sub>	gate-source cut-off voltage	I <sub>D</sub> = 200 μA; V <sub>DS</sub> = 15 V	-0.5	-	-7.5	V
I <sub>DSS</sub>	drain current	$V_{GS} = 0 V; V_{DS} = 15 V$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	-	250	mW
y <sub>fs</sub>	forward transfer admittance	$V_{GS} = 0 V; V_{DS} = 15 V$	4.5	-	-	mS



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## 2. Pinning information

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)		g → s
3	gate (g)		sym054

## 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BF556A	-	plastic surface mounted package; 3 leads	SOT23		
BF556B					
BF556C					

## 4. Marking

Table 4. Marking	
Type number	Marking code <sup>[1]</sup>
BF556A	24*
BF556B	25*
BF556C	26*

[1] \* = p: made in Hong Kong.

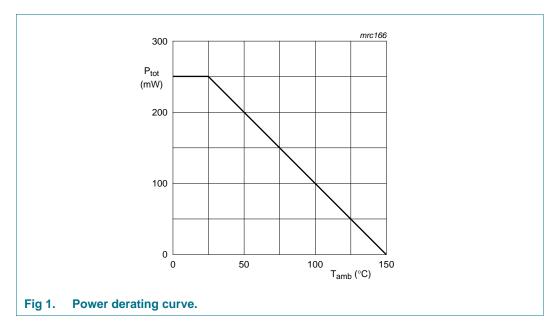
\* = t: made in Malaysia.

\* = W: made in China.

### 5. Limiting values

Table 5. In accordar	Limiting values nce with the Absolute Maximun	n Rating System (IE	EC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage (DC)		-	±30	V
V <sub>GSO</sub>	gate-source voltage	open drain	-	-30	V
$V_{GDO}$	gate-drain voltage (DC)	open source	-	-30	V
l <sub>G</sub>	forward gate current (DC)		-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$	<u>[1]</u> _	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

 Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm<sup>2</sup>.



### 6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm<sup>2</sup>.

BF556A\_BF556B\_BF556C

## 7. Static characteristics

#### Table 7. Static characteristics

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

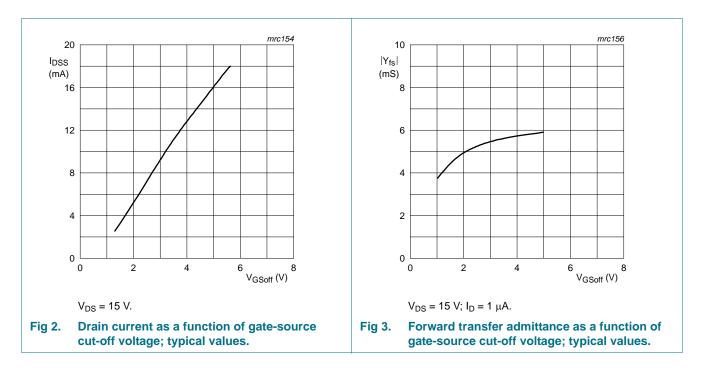
,	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)GSS</sub>	gate-source breakdown voltage	$I_G = -1 \ \mu A; \ V_{DS} = 0 \ V$	-30	-	-	V
V <sub>GSoff</sub>	gate-source cut-off voltage	$I_D = 200 \ \mu A; \ V_{DS} = 15 \ V$	-0.5	-	-7.5	V
I <sub>DSS</sub> drain current	$V_{GS} = 0 V; V_{DS} = 15 V$					
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
I <sub>GSS</sub>	gate-source leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-0.5	-5000	pА
y <sub>fs</sub>	forward transfer admittance	$V_{GS} = 0 V; V_{DS} = 15 V$	4.5	-	-	mS
y <sub>os</sub>	common source output admittance	$V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 15 \text{ V}$	-	40	-	μS

### 8. Dynamic characteristics

#### Table 8. Dynamic characteristics

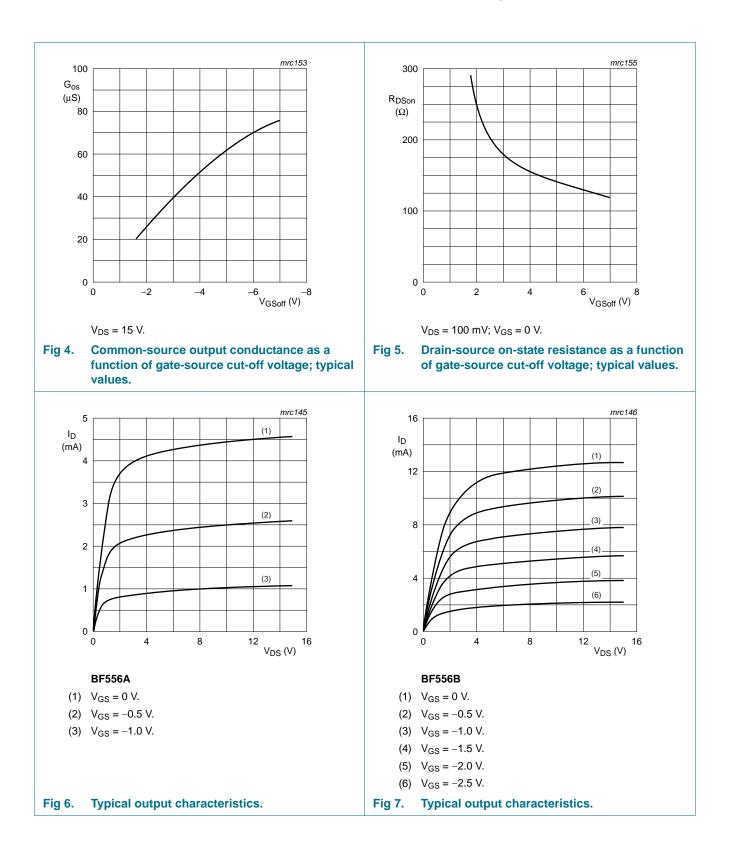
 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub> in	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz				
		$V_{GS} = -10 V$	-	1.7	-	pF
		$V_{GS} = 0 V$	-	3	-	pF
C <sub>rss</sub> re	reverse transfer capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz				
		$V_{GS} = -10 V$	-	0.8	-	pF
	$V_{GS} = 0 V$	-	0.9	-	pF	
g <sub>is</sub> common source input conductance	•	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
		f = 100 MHz	-	15	-	μS
		f = 450 MHz	-	300	-	μS
g <sub>fs</sub> common source transfer conductance	common source transfer conductance	$V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}$				
		f = 100 MHz	-	2	-	mS
		f = 450 MHz	-	1.8	-	mS
g <sub>rs</sub> comm	common source reverse	$V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}$	-	-6	-	μS
	conductance	f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
g <sub>os</sub>	common source output	$V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS
Vn	equivalent input noise voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1 mA; f = 100 Hz	-	40	-	nV/√Hz



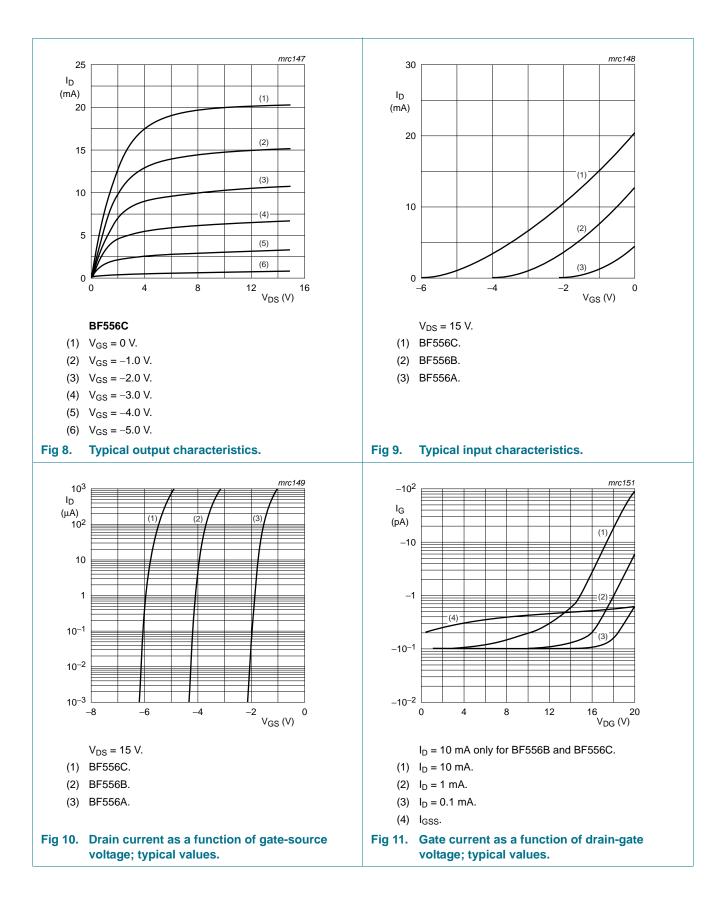
# BF556A; BF556B; BF556C

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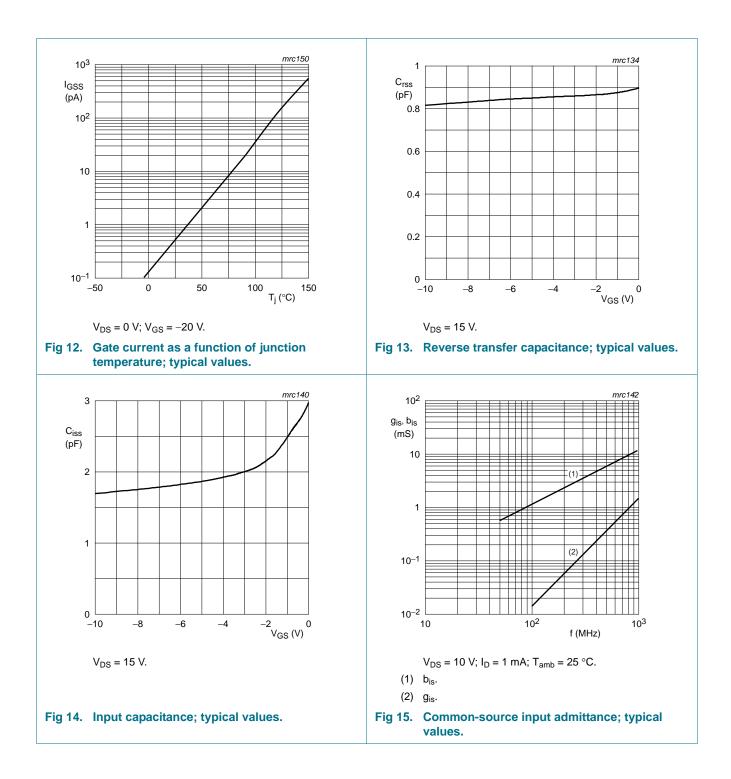
## BF556A; BF556B; BF556C

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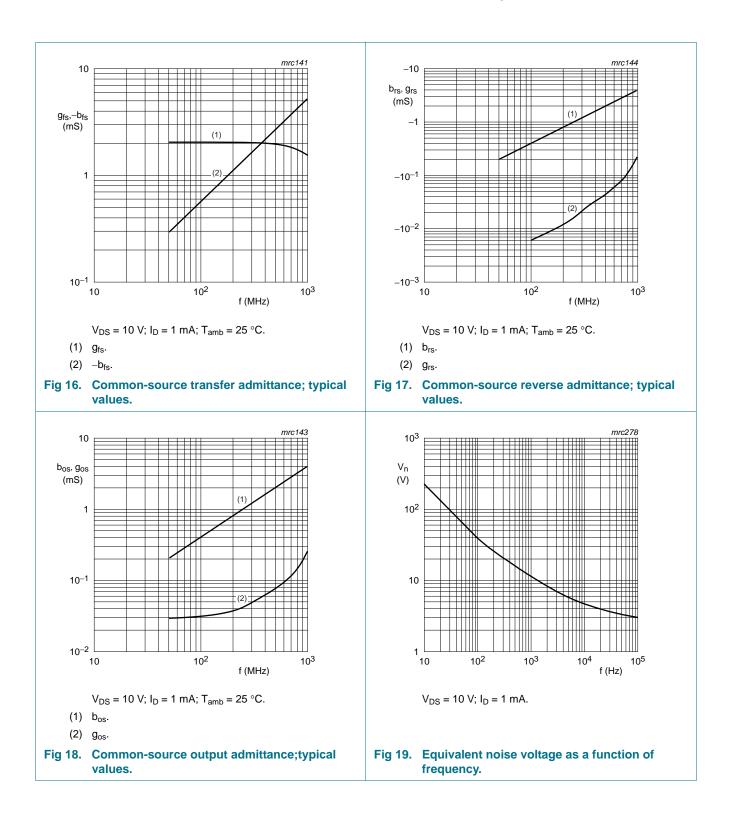
## BF556A; BF556B; BF556C

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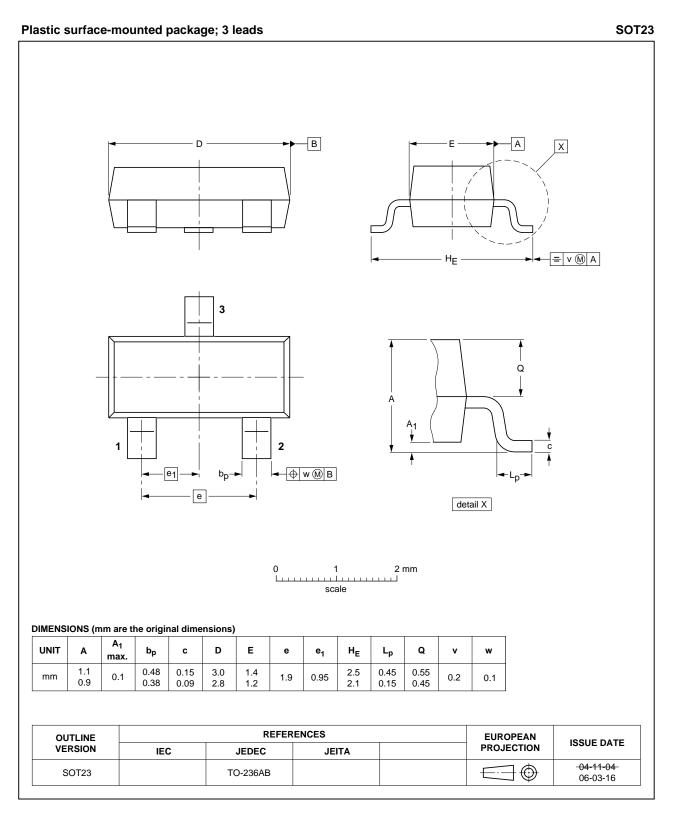
## BF556A; BF556B; BF556C

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### 9. Package outline



#### Fig 20. Package outline.

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## **10. Revision history**

Table 9.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BF556A_BF556B_BF556C v.4	20110915	Product data sheet	-	BF556A_BF556B_BF556C v.3
Modifications:		of this data sheet has be of NXP Semiconductors.	en redesigned to	comply with the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to th	e new company n	ame where appropriate.
	<ul> <li>Package ou</li> </ul>	tline drawings have bee	n updated to the la	atest version.
BF556A_BF556B_BF556C v.3 (9397 750 13393)	20040805	Product data sheet	-	BF556A-B-C v.2
BF556A-B-C v.2	19960729	Product data sheet	-	-

### 11. Legal information

### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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